

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2	"6440864".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 12:37
L2	2	"5545289".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 11:45
L3	11	remove near polymer near resist	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 11:47
L4	0	clean near polymer near leave near resist	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 11:47
L5	0	clean near polymer near resist	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 11:48
L6	1023487	clean resist	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 11:48
L7	115	clean adj resist	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 11:49
L8	9	clean near resist near surface	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 12:26
L9	2	"6677286".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 12:36

EAST Search History

L10	0	A method of patterning a metal layer that cleans the residue from a metal etch process without removing a photoresist etch "mask."	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/09/19 12:36
L11	0	method patterning metal layer cleans residue without removing mask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	NEAR	ON	2006/09/19 12:37
L12	0	cleans residue without removing mask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	NEAR	ON	2006/09/19 12:37
L13	2	"6542282".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 12:52
L14	223497	etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 12:52
L15	2	ysilicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 12:52
L16	128595	polysilicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 12:52
L17	2196	BARC	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 12:52
L18	4582	residue near removal	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 12:52
L19	452761	resist	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 12:53

EAST Search History

L20	116341	ash	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 12:53
L21	122177	ash or (resist adj removal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 12:53
L22	111	14 and 16 and 18 and 21	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 12:55
L23	249940	fluorine	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 12:55
L24	865824	oxygen	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 12:55
L25	100280	23 and 24	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 12:55
L26	525586	plasma	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 12:55
L27	72	25 and 22	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 12:56
L28	71	26 and 27	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 13:28
L29	0	remove residue before resist	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	NEAR	ON	2006/09/19 15:58

EAST Search History

L30	2	"6759179".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	NEAR	ON	2006/09/19 13:41
L31	410	16 and 17 and 19	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	NEAR	ON	2006/09/19 13:42
L32	30286	23 and 24 and 26	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	NEAR	ON	2006/09/19 13:42
L33	78	31 and 32	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	NEAR	ON	2006/09/19 13:42
L34	9117	remove residue	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	NEAR	ON	2006/09/19 13:42
L35	16	33 and 34	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	NEAR	ON	2006/09/19 13:48
L36	2	"5804088".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	NEAR	ON	2006/09/19 14:42
L37	90	BARC near resist	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	NEAR	ON	2006/09/19 14:42
L38	0	polysilicon near 37	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	NEAR	ON	2006/09/19 14:42
L39	7	polysilicon with 37	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	NEAR	ON	2006/09/19 14:50

EAST Search History

L40	2	"6542282".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	NEAR	ON	2006/09/19 15:19
L41	2	"6010829".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	NEAR	ON	2006/09/19 14:51
L42	0	resist near sidewall near (polymer and residue)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	NEAR	ON	2006/09/19 15:19
L43	5	resist near sidewall with (polymer and residue)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	NEAR	ON	2006/09/19 15:58
L44	1244	216/41	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	NEAR	ON	2006/09/19 15:58
L45	168	remove resist residue	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	NEAR	ON	2006/09/19 15:59
L46	1	44 and 45	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	NEAR	ON	2006/09/19 15:58
L47	3842	remove polymer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	NEAR	ON	2006/09/19 15:59
L48	14	44 and 47	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	NEAR	ON	2006/09/19 15:59